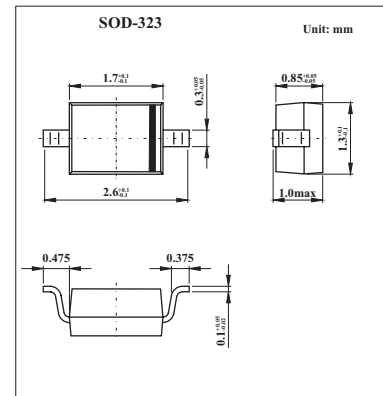


1PS76SB62

■ Features

- Ultra high swiching speed
- Very low capacitance
- High breakdown voltage
- Guard ring protected
- Two pin very small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25 °C

PARAMATER	SYMBOL	MIN	MAX	UNIT
continuous reverse voltage	V _R		4	V
continuous forward current	I _F		20	mA
storage temperature	T _{stg}	-65	+150	°C
junction temperature	T _j		125	°C
operating ambient temperature	T _{amb}	-65	+125	°C

■ Electrical Characteristics Ta = 25 °C

PARAMATER	SYMBOL	CONDITIONS	MAX	UNIT
forward voltage	V _F	I _F = 2 mA; Note 1	800	mV
reverse current	I _R	V _R = 40 V; note 1	1	μ A
diode capacitance	C _d	V _R = 0 V; f = 1 MHz	0.6	pF
thermal resistance from junction to ambient	R _{thj-a}		450	K/W

Note:

1.Pulse test: pulse width = 300 μ s; δ = 0.02.

■ Marking

Marking	S6
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